

Silicon PNP Power Transistors

2SB337

DESCRIPTION

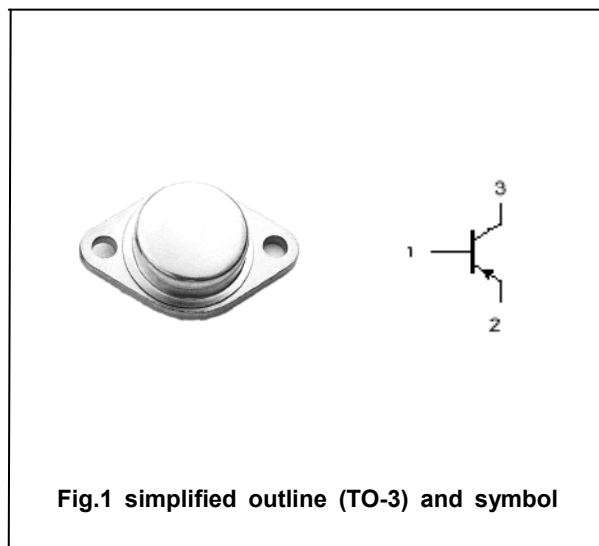
- With TO-3 package
- Low collector saturation voltage

APPLICATIONS

- For audio frequency power output applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-40	V
V _{CEO}	Collector-emitter voltage	Open base	-30	V
V _{EBO}	Emitter-base voltage	Open collector	-10	V
I _C	Collector current		-7	A
I _E	Emitter current		7	A
I _B	Base current		-1	A
P _C	Collector power dissipation	T _C ≤55□	30	W
T _j	Junction temperature		100	□
T _{stg}	Storage temperature		-55~100	□

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-10mA; I _B =0	-30			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-1mA; I _C =0	-10			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-4A; I _B =-0.4A		-0.29		V
V _{BE}	Base-emitter on voltage	I _C =-1A; V _{CE} =-2V		-0.38		V
I _{CBO}	Collector cut-off current	V _{CB} =-30V; I _E =0			-0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-10V; I _E =0			-0.1	mA
h _{FE}	DC current gain	I _C =-1A; V _{CE} =-2V	50	90	165	

◆ h_{FE} Classifications

A	B
50-100	80-165

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PACKAGE OUTLINE

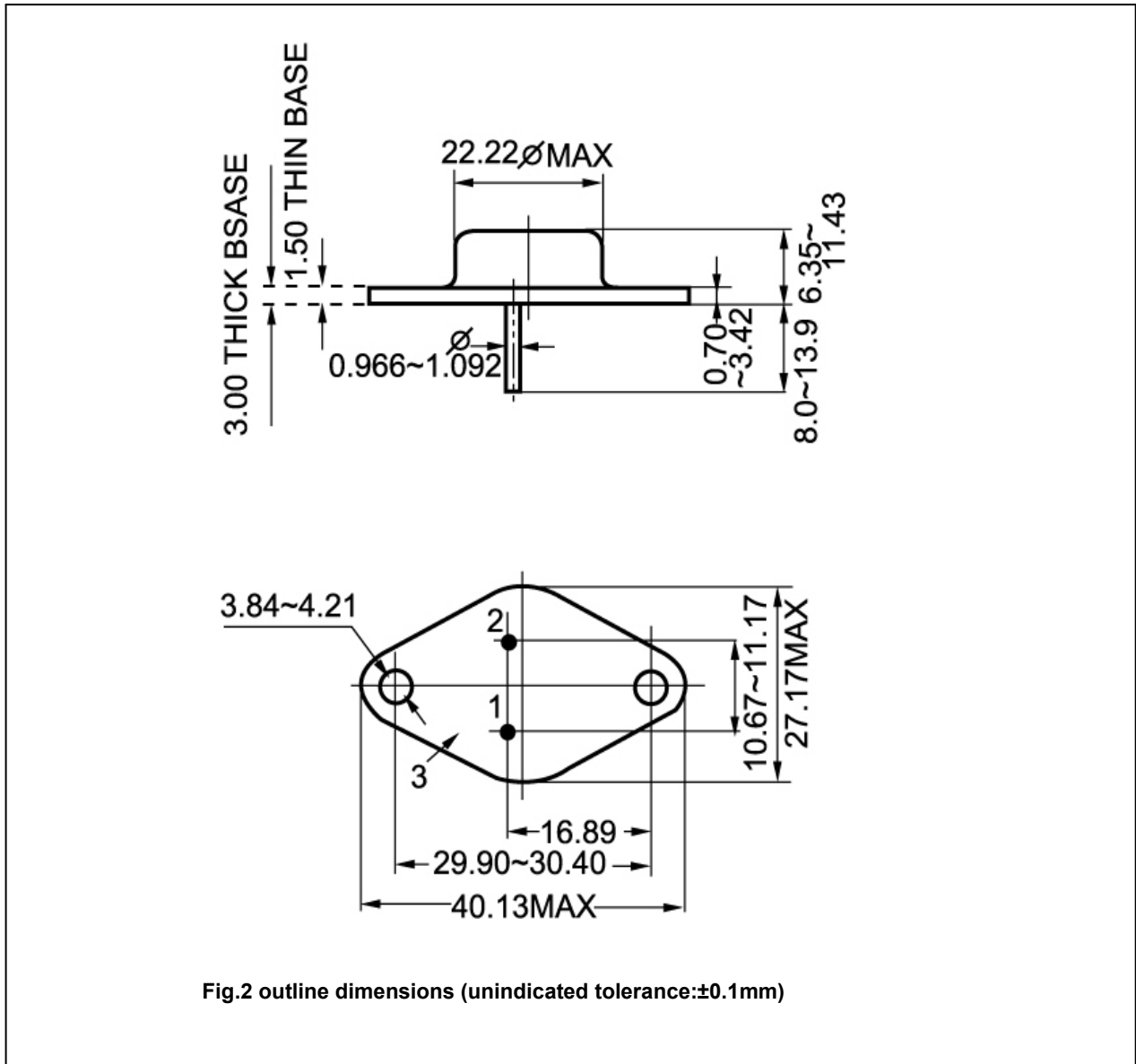


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)